



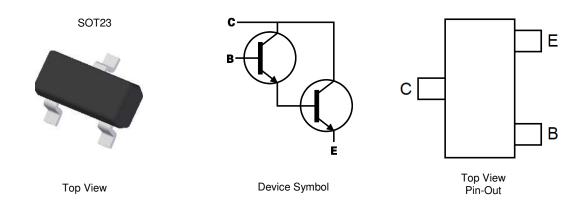
40V NPN DARLINGTON TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.008 grams (Approximate)



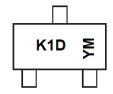
Ordering Information (Note 4)

Part Number	Doolsono	Marking	Reel Size (inches) Tape Width (mm)		Pac	cking
Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Qty.	Carrier
MMBT6427-7-F	SOT23	K1D	7	8	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



$$\begin{split} & \text{K1D} = \text{Product Type Marking Code} \\ & \text{YM} = \text{Date Code Marking} \\ & \text{Y or } \overline{\text{Y}} = \text{Year (ex: K} = 2023) \\ & \text{M or } \overline{\text{M}} = \text{Month (ex: 9} = \text{September)} \end{split}$$

Date Code Key

Year	2010	-	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	Χ	-	K	L	М	N	Р	R	S	T	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@ T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	V _{EBO}	12	V
Collector Current	Ic	500	mA
Peak Collector Current	Ісм	1	Α

Thermal Characteristics (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D-	310	mW
Fower Dissipation	(Note 6)	P _D	350	IIIVV
Thermal Desigtance Junction to Ambient	(Note 5)	Б	403	0000
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	357	°C/W
Thermal Resistance, Junction to Leads	(Note 7)	R ₀ JL	350	°C/W
Thermal Resistance, Junction to Case (Note 5)		Rejc	120	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

^{5.} For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

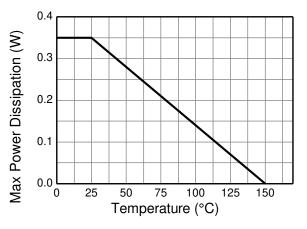
^{6.} Same as note (5), except the device is mounted on 15mm x 15mm 1oz copper.

^{7.} Thermal resistance from junction to solder-point (at the end of the leads).

^{8.} Refer to JEDEC specification JESD22-A114, JESD22-A115 and JES-022-C101.



Thermal Characteristics and Derating Information



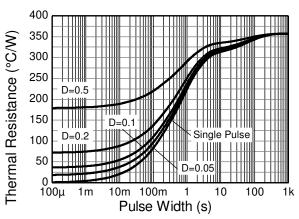
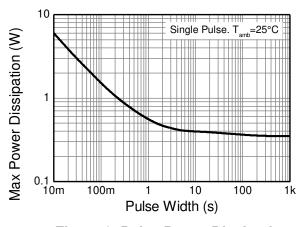


Figure 1. Derating Curve

Figure 2. Transient Thermal Impedance



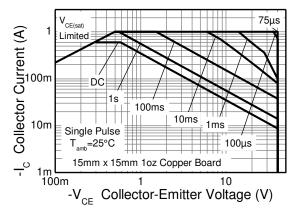


Figure 3. Pulse Power Dissipation

Figure 4. Safe Operating Area



Electrical Characteristics (@ T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	40	170	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	40	66	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	12	17	_	V	I _E = 100μA
Collector Cutoff Current	Ісво	_	1	50	nA	V _{CB} = 30V
Collector Cutoff Current	Ices	_	0.03	1	μΑ	V _{CE} = 25V
Emitter Cutoff Current	I _{EBO}	_	1	50	nA	V _{EB} = 10V
ON CHARACTERISTICS (Note 9)		•				
DC Current Gain	hFE	10,000 20,000 14,000	100,000 —	100,000 200,000 140,000	_	I _C = 10mA, V _{CE} = 5V I _C = 100mA, V _{CE} = 5V I _C = 500mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage	VCE(sat)	_	0.68 0.87	1.2 1.5	V	Ic = 50mA, I _B = 0.5mA Ic = 500mA, I _B = 0.5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	1.55	2	V	I _C = 500mA, I _B = 0.5mA
Base-Emitter On Voltage	V _{BE(on)}	_	1.25	1.75	V	Ic = 50mA, VcE = 5V

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



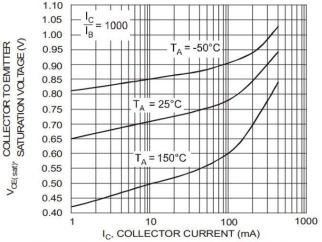


Fig. 5, Collector Emitter Saturation Voltage vs. Collector Current

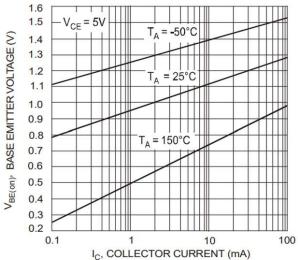


Fig. 7, Base Emitter Voltage vs. Collector Current

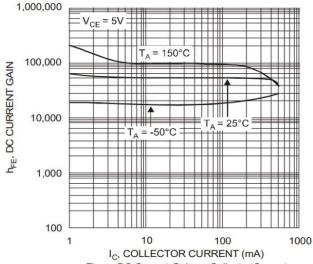


Fig. 6, DC Current Gain vs Collector Current

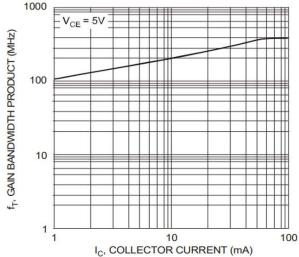


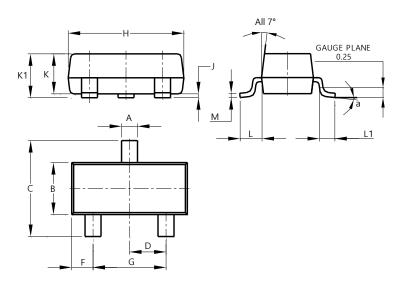
Fig. 8, Gain Bandwidth Product vs Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

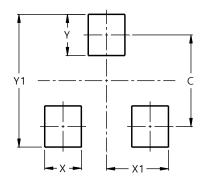


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
٦	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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